








	<h2>SI7459DP-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI7459DP-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 30V 13A PPAK SO-8</p> <p>Datenblätter:  SI7459DP-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 1000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7459DP-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 30V 13A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	1000 pcs Stock
detaillierte Beschreibung	P-Channel 30V 13A (Ta) 1.9W (Ta) Surface Mount
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	1.9W (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	13A (Ta)
Rds On (Max) @ Id, Vgs	6.8 mOhm @ 22A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	170nC @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±25V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7459DP-T1-GE3TR

SI7459DP-T1-GE3 ist neu im Original, Suche SI7459DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7459DP-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7459DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7459DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 13A PPAK SO-8</p>	 <p>SI7458DP-T1-GE3 Vishay Precision Group SI7458DP-T1-GE3 VISHAY</p>	 <p>SI7459BDP-GE3 VISHAY VISHAY QFN</p>	 <p>SI7459DP-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 13A PPAK SO-8</p>
 <p>SI7460DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 60V 11A PPAK SO-8</p>	 <p>SI7460DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 60V 11A PPAK SO-8</p>	 <p>SI7460DP-T1-E3 Vishay / Siliconix MOSFET N-CH 60V 11A PPAK SO-8</p>	 <p>SI7459DP-T1-E3 Vishay / Siliconix MOSFET P-CH 30V 13A PPAK SO-8</p>

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SI7452DP-T1-E3	SI7452DP-T1-GE3	SI7452DP-T1-GE3	SI7452DP-T1-GE3	SI7454CDP-T1-GE3
SI7454CDP-T1-GE3	SI7454DDP-T1-GE3	SI7454DDP-T1-GE3	SI7454DP	SI7454DP-T1-E3
SI7454DP-T1-E3	SI7454DP-T1-GE3	SI7454DP-T1-GE3	SI7456CDP-T1-GE3	SI7456CDP-T1-GE3
SI7456DDP-T1-GE3	SI7456DDP-T1-GE3	SI7456DP	SI7456DP-T1-E3	SI7456DP-T1-E3
SI7456DP-T1-GE3	SI7456DP-T1-GE3	SI7458DP-T1-E3	SI7459DP-T1-E3	SI7459DP-T1-E3
SI7459DP-T1-GE3	SI7460DP	SI7460DP-T1-E3	SI7460DP-T1-E3	SI7460DP-T1-GE3
SI7460DP-T1-GE3	SI7461DP-T1-E3	SI7461DP-T1-E3	SI7461DP-T1-GE3	SI7461DP-T1-GE3
SI7462DP-T1-E3	SI7462DP-T1-E3	SI7462DP-T1-GE3	SI7462DP-T1-GE3	SI7463ADP-T1-GE3
SI7463ADP-T1-GE3	SI7463DP-T1-GE3	SI7463DP-T1-GE3	SI7464DP-T1-E3	SI7464DP-T1-E3
SI7464DP-T1-GE3	SI7464DP-T1-GE3	SI7465DP-T1-E3	SI7465DP-T1-E3	SI7465DP-T1-GE3

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